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DECDES

DRDNB21D

COMPLEX ARRAY FOR DUAL RELAY DRIVER

Features

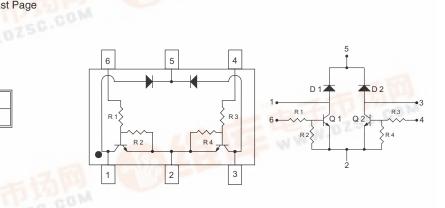
- Epitaxial Planar Die Construction
- Two Pre-Biased Transistors and Two Switching Diodes, Internally Connected in One Package
- Ideally Suited for Automated Assembly Processes
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Last Page
- Ordering Information: See Last Page
- Weight: 0.006 grams (approximate)

R1 = R3 = $2.2k\Omega$ (nominal) R2 = R4 = $47k\Omega$ (nominal)

1.5.5	1.01	1						
SOT-363								
Dim	Min	Max						
Α	0.10	0.30						
В	1.15	1.35						
С	2.00	2.20						
D	0.65 N	ominal						
F	0.30	0.40						
н	1.80	2.20						
J		0.10						
К	0.90	1.00						
Ľ	0.25	0.40						
М	0.10	0.25						
α	0°	8°						
All Dir	nensions	in mm						



Maximum Ratings, Total Device @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	Pd	200	mW
Thermal Resistance, Junction to Ambient Air (Note 3)	R _{0JA}	625	°C/W
Operating and Storage Junction Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, Pre-Biased NPN Transistor @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CC}	50	V
Collector-Emitter Voltage	V _{in}	-5 to +12	V
Emitter-Base Voltage	Ι _Ο	100	mA
Output Current - Continuous (Note 3)	Ic	200	mA

1. No purposefully added lead.

Notes:

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2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

PDF Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested p



Maximum Ratings, Switching Diode @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current (Note 3)	I _{FM}	500	mA
Average Rectified Output Current (Note 3)	Ι _Ο	250	mA
Non-Repetitive Peak Forward Surge Current $@ t = 1.0 \mu s$ @ t = 1.0s	I _{FSM}	4.0 2.0	А

Electrical Characteristics, Pre-Biased NPN Transistor @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltogo	V _{I(off)}	0.5	_	_	V	$V_{CC} = 5V, I_{O} = 100 \mu A$
Input Voltage	VI(on)	—	_	1.1	V	$V_{O} = 0.3V, I_{O} = 5mA$
Output Voltage	V _{O(on)}		_	0.3	V	$I_{O}/I_{I} = 50 \text{mA}/0.25 \text{mA}$
Input Current	I _I		_	3.6	mA	$V_1 = 5V$
Output Current	I _{O(off)}	_	_	0.5	uA	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	GI	80	_	_	—	V _O = 5V, I _O = 10mA
Input Resistor Tolerance	ΔR1	-30	_	+30	%	
Resistance Ratio Tolerance	∆R2/R1	-20	_	+20	%	
Gain-Bandwidth Product*	f⊤	_	250	_	MHz	$V_{CE} = 10V$, $I_E = 5mA$, f = 100MHz

* Transistor - For Reference Only

Electrical Characteristics, Switching Diode @ T_A = 25°C unless otherwise specified

Characteristic		Min	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 4)	V _{(BR)R}	75	_	V	I _R = 10μA
Forward Voltage (Note 4)	V _F	0.62	0.72 0.855 1.0 1.25	V	I _F = 5.0mA I _F = 10mA I _F = 100mA I _F = 150mA
Reverse Current (Note 4)	I _R		2.5 50 30 25	μΑ μΑ μΑ nA	
Total Capacitance	Ст		4.0	pF	V _R = 0, f = 1.0MHz
Reverse Recovery Time	t _{rr}	_	4.0	ns	$\label{eq:lf} \begin{array}{l} I_F = I_R = 10 m A, \\ I_{rr} = 0.1 \ x \ I_R, \ R_L = 100 \Omega \end{array}$

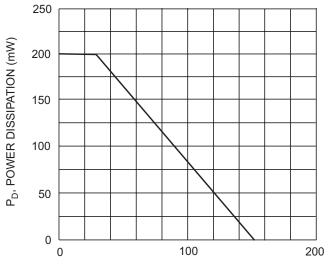
Notes:

3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

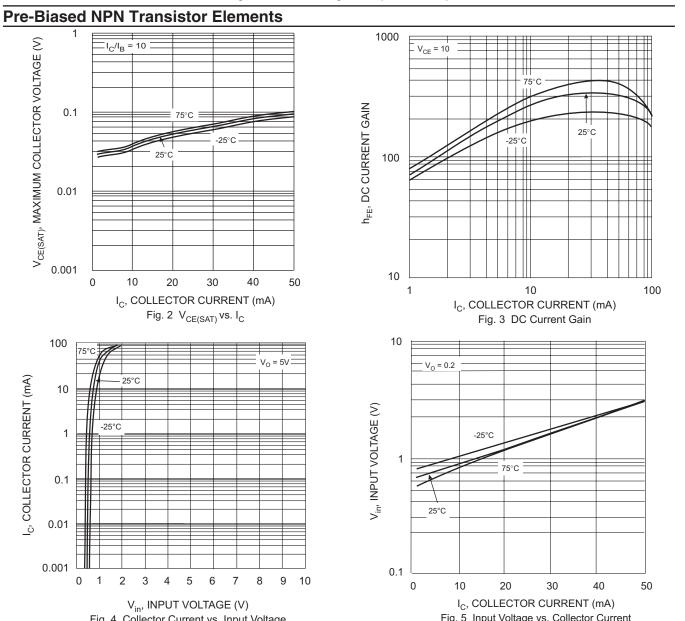
4. Short duration pulse test used to minimize self-heating effect.



Device Characteristics

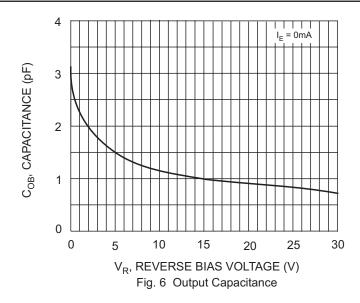


T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Power Derating Curve (Total Device)





Pre-Biased NPN Transistor Elements (Continued)





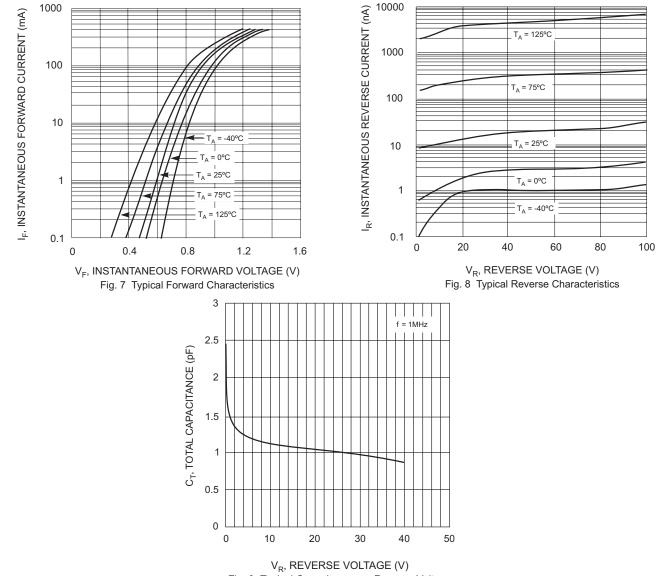
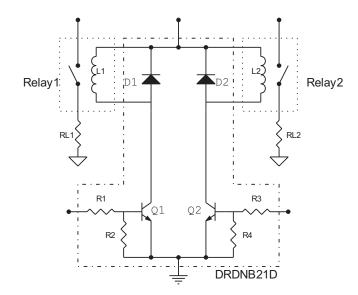


Fig. 9 Typical Capacitance vs. Reverse Voltage



Typical Application Circuit



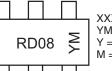
Typical Application Circuit using DRDNB21D with two independent relays.

Ordering Information (Note 5)

Device	Marking Code	Packaging	Shipping
DRDNB21D-7	RD08	SOT-363	3000/Tape & Reel

Notes: 5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



 $\begin{array}{l} XXXX = \mbox{Product Type Marking Code} \\ YM = \mbox{Date Code Marking} \\ Y = \mbox{Year, e.g., T} = 2006 \\ M = \mbox{Month, e.g., 1} = \mbox{January} \end{array}$

Date Code Key

	٢	Year				2005	200	6	2007	2008		2009
	C	Code				S	Т		U	V		W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

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